2SC1846

Silicon NPN epitaxial planar type

For medium output power amplification Complementary to 2SA0885

■ Features

- ullet Low collector-emitter saturation voltage $V_{CE(sat)}$
- Output of 3 W can be obtained by a complementary pair with 2SA0885
- TO-126B package which requires no insulation plate for installation to the heat sink

■ Absolute Maximum Ratings T

				0.75	ا ا ا مین		
Parameter	Symbol	Rating	Unit	<u>0.75</u>	0.5±0.1	0.5±0.1	1.76±0.
Collector-base voltage (Emitter open)	V_{CBO}	45	V		2.3±0.2		
Collector-emitter voltage (Base open)	V _{CEO}	35	V		1 2 3		: Emitter : Collecte
Emitter-base voltage (Collector open)	V _{EBO}	5	V	colli a		3	: Base
Collector current	I_{C}	1	A	7/0)	TO-126B-A	.1 Packag
Peak collector current	I _{CP}	1.5	A	Mes 14	_		200
Collector power dissipation	P _C	1.2	WO	* ~ C ~ C ~ C ~ C ~ C ~ C ~ C ~ C ~ C ~	e _O)ي	260
		5.0 *	80110	SI, 16	×16,	in	
Junction temperature	$T_{\rm j}$	150	S °CXO	· · · · · · · · · · · · · · · · · · ·	· · · · · ·	S	
Storage temperature	T_{stg}	-55 to +150	°C	and alle	10° 21	10	
Note) *: With a $100 \times 100 \times 2$ mm Al h	neat sink	-0/0	40	y, Fill,	a. " Lo	CO	
11 + 6		100	, Yo,	011,160	1/2 CO2.	5	
■ Electrical Characteristics	$\Gamma_{\rm a} = 25\%$	± 3°C	Sil is	o dilli	yo ver		
Parameter	Symbo	10,000	Conditio	nş	Міп Тур	Max	Unit

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 1 \text{ mA}$ $I_E = 0$	Q 45			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	35			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 20 \text{ V}, I_{B} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$			10	μΑ
Forward current transfer ratio	h _{FE1} *	$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$	85		340	_
- inite	h _{FE2}	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$	50			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}$			0.5	V
Transition frequency	f	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			20	pF
(Common base, input open circuited)						

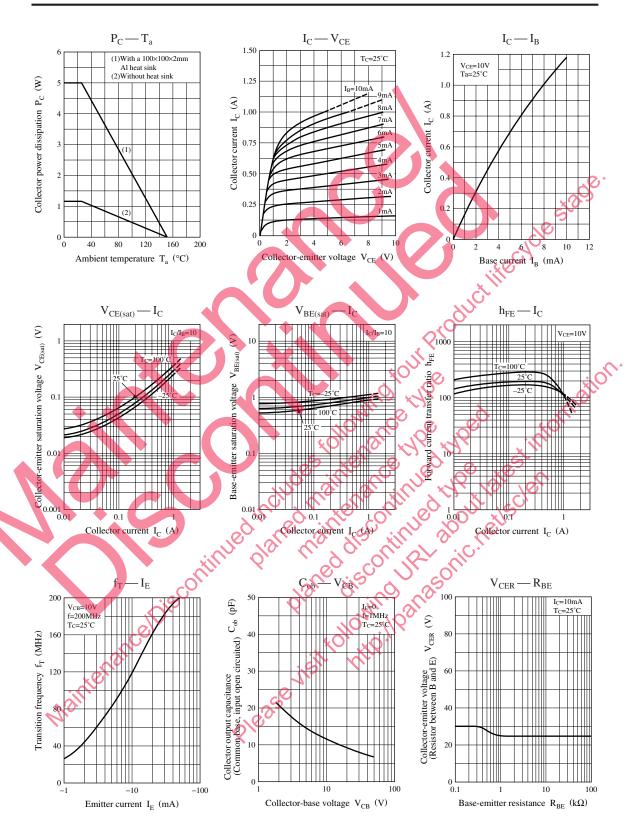
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Q	R	S	
h _{FE1}	85 to 170	120 to 240	170 to 340	

Unit: mm $8.0^{+0.5}_{-0.1}$ 3.2±0.2 1: Emitter 2: Collector 3: Base TO-126B-A1 Package

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